

Oral Presentation

[DES2]Driving Technology

Chair: Chih-Wen Lu (Nat. Tsing Hua Univ.)

Co-Chair: Keiichi Nakajima (Tianma Japan)

Wed. Nov 27, 2019 3:20 PM - 4:40 PM Room 207 (2F)

4:00 PM - 4:20 PM

[DES2-3]Highly Reliable a-IGZO TFT Gate Driver Circuit to Suppress Threshold Voltage Shift of Pull-down TFT

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Keywords:Oxide TFT, Gate Driver Circuit, Reliability, Duty Ratio

We present the highly reliable gate driver circuit using AC-driven method of a pull-down TFTs. Two pull-down TFTs are driven with duty ratio of 33.3% and 66.7%, respectively, VOUT discharge completely. The proposed circuit can minimize coupling noise by discharging the Q and VOUT node constantly except for output period.